

**APPENDIX****IN THE CLAIMS:**

Claims 1 and 7 have been amended as follows:

1. (Twice Amended) A semiconductor device, comprising:
a metal-oxide-semiconductor field-effect transistor that includes:
a gate insulation film and a gate electrode on the gate insulation film,
the gate electrode including a germanium film on the gate insulation film, wherein p-type impurities are doped into said germanium film.
7. (Twice Amended) A semiconductor device, comprising:
an n-channel metal-oxide-semiconductor field-effect transistor; and
a p-channel metal-oxide-semiconductor field-effect transistor,
at least one of the n-channel metal-oxide-semiconductor field-effect transistor
and the p-channel metal-oxide-semiconductor field-effect transistor including:
a gate insulation film and a gate electrode on the gate insulation film,
the gate electrode including a germanium film on the gate insulation film, wherein p-type impurities are doped into said germanium film.

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